**Product data sheet** 

# 1. General description

Planar passivated sensitive gate four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

### 2. Features and benefits

- · High blocking voltage capability
- Direct triggering from low power drivers and logic ICs
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Sensitive gate

# 3. Applications

- General purpose motor control
- · General purpose switching

#### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Values				Unit
Absolute	maximum rating						
$V_{DRM}$	repetitive peak off-state voltage		600				V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 99 °C; Fig. 1; Fig. 2; Fig. 3	16			А	
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig. 4; Fig. 5	155			А	
Symbol	Parameter	Conditions Min Typ Max					Unit
Static ch	aracteristics						
I <sub>GT</sub> gate trigger current		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-		2.5	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-		4	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-		5	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-		11	25	mA

**4Q Triac** 

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	
2	T2	main terminal 2		T2_DT1
3	G	gate		sym051
mb	T2	mounting base; main terminal 2		symosi

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package						
	Name	Description	Version				
BT139-600E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78				

# 7. Marking

**Table 4. Marking codes** 

Type number	Marking codes
BT139-600E	BT139-600E

**4Q Triac** 

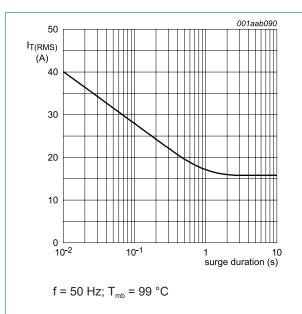
# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{DRM}$	repetitive peak off-state voltage		600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 99 ^{\circ}\text{C}$ ; Fig 1; Fig 2; Fig 3	16	А
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$ ; $t_p = 20 \text{ms}$ ; Fig 4; Fig 5	155	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$	170	А
l²t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	120	A <sup>2</sup> s
dl <sub>⊤</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 20 mA; T2+ G+	50	A/µs
		I <sub>G</sub> = 20 mA; T2+ G-	50	A/µs
		I <sub>G</sub> = 20 mA; T2- G-	50	A/µs
		I <sub>G</sub> = 50 mA; T2- G+	10	A/µs
I <sub>GM</sub>	peak gate current		2	А
$P_{GM}$	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T <sub>stg</sub>	storage temperature		-40 to 150	°C
T <sub>j</sub>	junction temperature		125	°C

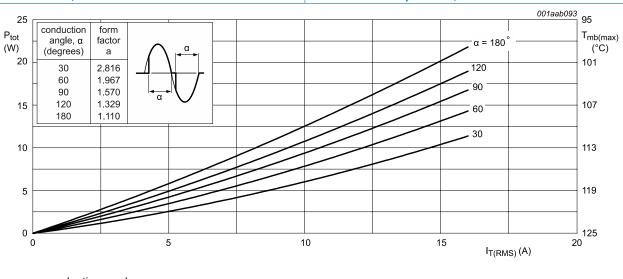
**4Q Triac** 



001aab091 20 I<sub>T(RMS)</sub> (A) (1) 10 5 150 T<sub>mb</sub> (°C) - 50 100 (1)  $T_{mb} = 99 \, ^{\circ}C$ 

Fig. 1. RMS on-state current as a function of surge duration; maximum values

Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

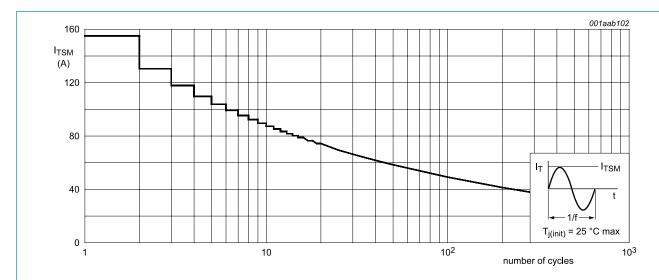


 $\alpha$  = conduction angle

 $a = form factor = I_{T(RMS)} / I_{T(AV)}$ 

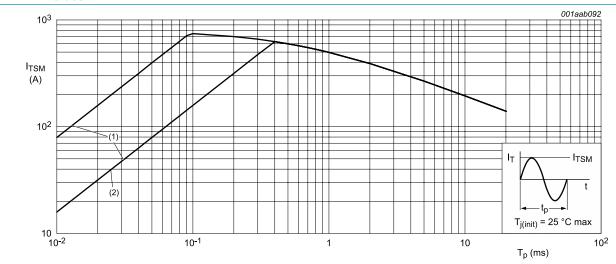
Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

**4Q Triac** 



f = 50 Hz; n = number of cycles

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



 $t_p \le 20 \text{ ms}$ 

(1) dl<sub>T</sub>/dt limit

(2) T2- G+ quadrant limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

**4Q Triac** 

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance	full cycle; Fig 6	-	-	1.2	K/W
	from junction to mounting base	half cycle; <u>Fig 6</u>	-	-	1.7	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W

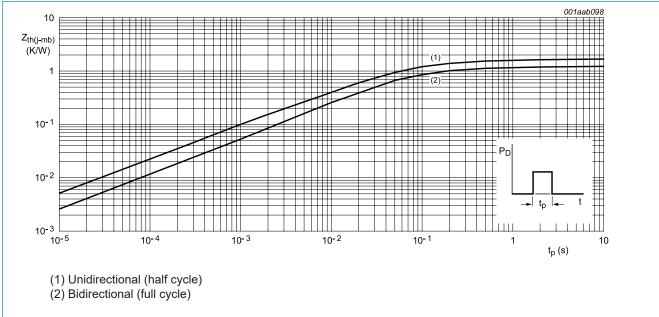


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

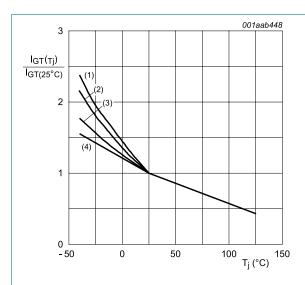
**4Q Triac** 

## 10. Characteristics

#### **Table 7. Characteristics**

<b>Symbol</b>	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+; $ $T_j = 25 \text{ °C}; Fig. 7$	-	2.5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	4	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	-	5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	-	11	25	mA
l <sub>L</sub>	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	3.2	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	16	40	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 8}}{\text{Fig. 8}}$	-	4	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; Fig. 8$	-	5.5	40	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	4	45	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.2	1.6	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	-	50	-	V/µs
<b>t</b> <sub>gt</sub>	gate-controlled turn-on time	$I_{TM} = 20 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

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- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

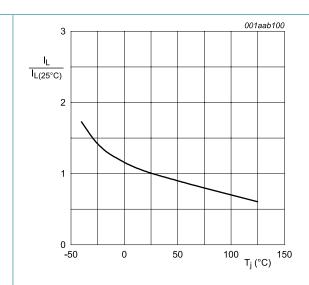


Fig. 8. Normalized latching current as a function of junction temperature

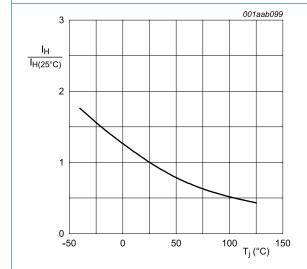
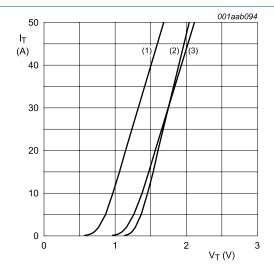


Fig. 9. Normalized holding current as a function of junction temperature

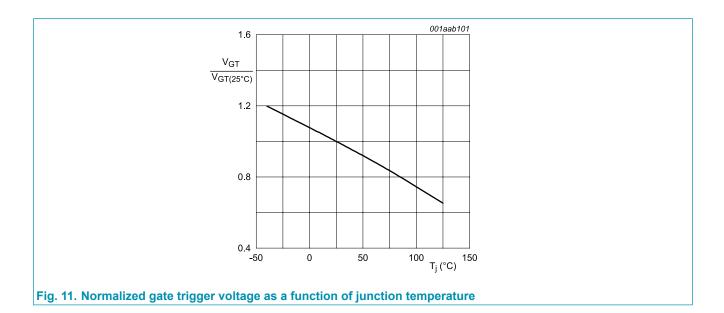


 $V_o = 1.195 \text{ V}; R_s = 0.018 \Omega$ 

- (1) T<sub>i</sub> = 125 °C; typical values
- (2)  $T_j = 125$  °C; maximum values
- (3)  $T_j = 25$  °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

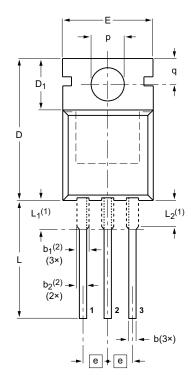
**4Q Triac** 

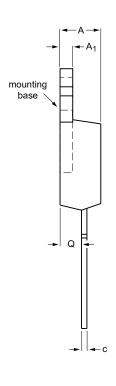


# 11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

**SOT78** 





#### **DIMENSIONS** (mm are the original dimensions)

UNIT	Α	A <sub>1</sub>	b	b <sub>1</sub> <sup>(2)</sup>	b <sub>2</sub> <sup>(2)</sup>	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> <sup>(1)</sup>	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

#### Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13

4Q Triad

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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For sales office addresses, please send an email to: salesaddresses@ween-semi.com
Date of release: 22 March 2018

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